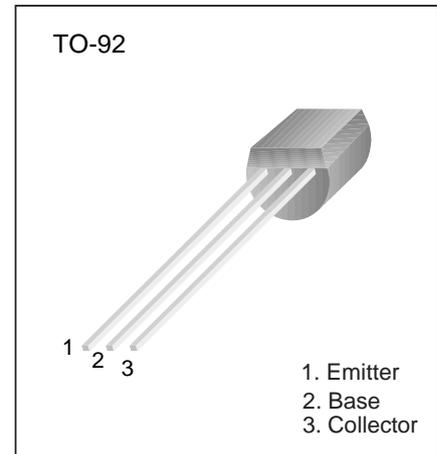


PNP General Purpose Amplifier 2N5401

■ Features

- Switching and amplification in high voltage
- Applications such as telephony
- Low current(max. 600mA)
- High voltage(max.150V)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-160	V
Collector-emitter voltage	V_{CEO}	-150	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current-continuous	I_c	-600	mA
Collector Power Dissipation	P_c	625	mW
Junction and storage temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c = -100 \mu\text{A}, I_E = 0$	-160			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = -1.0 \text{ mA}, I_B = 0$	-150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu\text{A}, I_c = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -120 \text{ V}, I_E = 0$			-50	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -3.0 \text{ V}, I_c = 0$			-50	nA
DC current gain	h_{FE}	$I_c = -1.0 \text{ mA}, V_{CE} = -5 \text{ V}$	50			
		$I_c = -10 \text{ mA}, V_{CE} = -5 \text{ V}$	60		240	
		$I_c = -50 \text{ mA}, V_{CE} = -5 \text{ V}$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -50 \text{ mA}, I_B = -5.0 \text{ mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_c = -50 \text{ mA}, I_B = -5.0 \text{ mA}$			-1.0	V
Transistor frequency	f_T	$V_{CE} = -5 \text{ V}, I_c = -10 \text{ mA}, f = 30 \text{ MHz}$	100		300	MHz